



#### 60V +175°C N-CHANNEL ENHANCEMENT MODE MOSFET

### **Product Summary**

BV <sub>DSS</sub>	R <sub>DS(ON)</sub> Max	I <sub>D</sub> Max T <sub>C</sub> = +25°C		
60V	50mΩ @ V <sub>GS</sub> = 10V	24A		
607	$65m\Omega @ V_{GS} = 4.5V$	21A		

#### **Features and Benefits**

- Rated to +175°C Ideal for High Ambient Temperature Environments
- 100% Unclamped Inductive Switching Ensures More Reliable and Robust End Application
- Low R<sub>DS(ON)</sub> Minimizes Power Losses
- Low Q<sub>G</sub> Minimizes Switching Losses
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability
- PPAP Capable (Note 4)

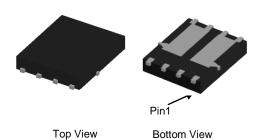
## **Description and Applications**

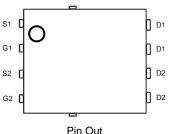
This MOSFET is designed to meet the stringent requirements of automotive applications. It is qualified to AEC-Q101, supported by a PPAP and is ideal for use in:

- Engine Management Systems
- Body Control Electronics
- DC-DC Converters

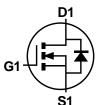
#### **Mechanical Data**

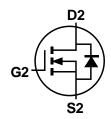
- Case: PowerDI<sup>®</sup>5060-8 (Type C)
- Case Material: Molded Plastic, "Green" Molding Compound.
  UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections Indicator: See Diagram
- Terminals: Finish Matte Tin Annealed over Copper Leadframe.
  Solderable per MIL-STD-202, Method 208 <sup>3</sup>
- Weight: 0.097 grams (Approximate)





Top View





Equivalent Circuit

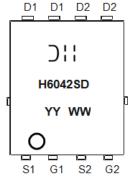
## Ordering Information (Note 5)

Part Number	Case	Packaging	
DMNH6042SPDQ-13	PowerDI5060-8 (Type C)	2,500/Tape & Reel	

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
- 2. See http://www.diodes.com/quality/lead\_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. Automotive products are AEC-Q101 qualified and are PPAP capable. Refer to http://www.diodes.com/quality/product\_compliance\_definitions/.
- 5. For packaging details, go to our website at http://www.diodes.com/products/packages.html.

## **Marking Information**



⊃¦¦ = Manufacturer's Marking H6042SD = Product Type Marking Code YYWW = Date Code Marking YY = Year (ex: 16 = 2016) WW = Week (01 to 53)



# **Maximum Ratings** (@ $T_A = +25^{\circ}C$ , unless otherwise specified.)

Characteristic	Symbol	Value	Unit		
Drain-Source Voltage	V <sub>DSS</sub>	60	V		
Gate-Source Voltage	$V_{GSS}$	±20	V		
Continuous Drain Current (Note 7) V <sub>GS</sub> = 10V	Steady State	$T_A = +25$ °C $T_A = +70$ °C	I <sub>D</sub>	5.7 4.6	А
Continuous Drain Current (Note 8) V <sub>GS</sub> = 10V	Steady State	$T_{C} = +25^{\circ}C$ $T_{C} = +100^{\circ}C$	I <sub>D</sub>	24 17	А
Pulsed Drain Current (10µs Pulse, Duty Cycle = 1%)	I <sub>DM</sub>	32	Α		
Maximum Continuous Body Diode Forward Current (	I <sub>S</sub>	24	Α		
Avalanche Current (Note 9) L = 10mH	I <sub>AS</sub>	3.5	Α		
Avalanche Energy (Note 9) L = 10mH	E <sub>AS</sub>	65	mJ		

## Thermal Characteristics (@TA = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit	
Total Power Dissipation (Note 6)	P <sub>D</sub>	1.2	W	
Thermal Resistance, Junction to Ambient (Note 6)	Steady State	D	105	°C/W
Thermal Resistance, Junction to Ambient (Note 6)	t<10s	$R_{ heta JA}$	54	
Total Power Dissipation (Note 7)		P <sub>D</sub>	2.5	W
Thermal Resistance, Junction to Ambient (Note 7)		Б	51	
Thermal Resistance, Junction to Ambient (Note 7)	t<10s	$R_{\theta JA}$	26	°C/W
Thermal Resistance, Junction to Case (Note 8)	$R_{ heta JC}$	3.5		
Operating and Storage Temperature Range		$T_{J,}T_{STG}$	-55 to +175	°C

Notes:

- 6. Device mounted on FR-4 PC board, with minimum recommended pad layout, single sided.7. Device mounted on FR-4 substrate PC board, 2oz copper, with thermal bias to bottom layer 1-inch square copper plate.8. Thermal resistance from junction to soldering point (on the exposed drain pad).
- 9.  $I_{AS}$  and  $E_{AS}$  ratings are based on low frequency and duty cycles to keep  $T_J = +25^{\circ}C$ .

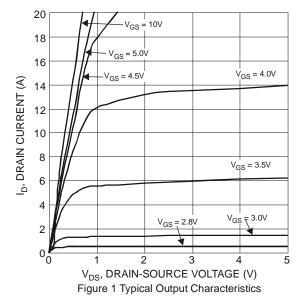


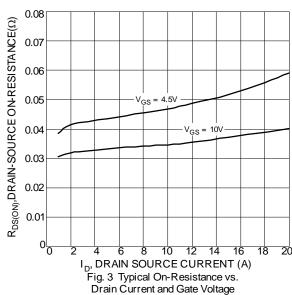
## Electrical Characteristics (@T<sub>A</sub> = +25°C, unless otherwise specified.)

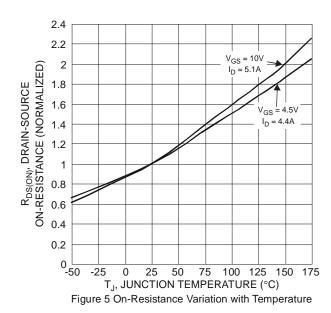
Characteristic		Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 10)							
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	60	_	_	V	$V_{GS} = 0V, I_D = 250\mu A$	
Zero Gate Voltage Drain Current T <sub>J</sub> = +25°C	I <sub>DSS</sub>	_	_	1	μA	V <sub>DS</sub> = 60V, V <sub>GS</sub> = 0V	
Gate-Source Leakage		_	_	±100	nA	$V_{GS} = \pm 20V, V_{DS} = 0V$	
ON CHARACTERISTICS (Note 10)	•			•	•		
Gate Threshold Voltage	V <sub>GS(TH)</sub>	1.0	_	3.0	V	$V_{DS} = V_{GS}$ , $I_D = 250\mu A$	
Static Drain-Source On-Resistance	7	_	34	50	mΩ	$V_{GS} = 10V, I_D = 5.1A$	
Static Dialit-Source Off-Resistance	R <sub>DS(ON)</sub>		45	65	11177	V <sub>GS</sub> = 4.5V, I <sub>D</sub> = 4.4A	
Diode Forward Voltage	$V_{SD}$		0.8	1.2	V	$V_{GS} = 0V, I_S = 2.6A$	
DYNAMIC CHARACTERISTICS (Note 11)				•			
Input Capacitance	C <sub>ISS</sub>	_	584	_	pF	.,	
Output Capacitance	Coss	_	83	_	pF	$V_{DS} = 25V, V_{GS} = 0V,$ f = 1.0MHz	
Reverse Transfer Capacitance	C <sub>RSS</sub>	_	24	_	pF	11 = 1.0WH2	
Gate Resistance	R <sub>G</sub>	_	3.8	_	Ω	$V_{DS} = 0V$ , $V_{GS} = 0V$ , $f = 1MHz$	
Total Gate Charge (V <sub>GS</sub> = 4.5V)	Q <sub>G</sub>	_	4.2	_	nC		
Total Gate Charge (V <sub>GS</sub> = 10V)	$Q_{G}$	_	8.8	_	nC	141/ 1 504	
Gate-Source Charge	$Q_{GS}$	_	1.8	_	nC	$V_{DS} = 44V, I_D = 5.2A$	
Gate-Drain Charge	$Q_{GD}$	_	1.8	_	nC	1	
Turn-On Delay Time	t <sub>D(ON)</sub>		3.4	_	ns		
Turn-On Rise Time	t <sub>R</sub>	_	1.9	_	ns	$V_{GS} = 10V, V_{DS} = 30V,$	
Turn-Off Delay Time	t <sub>D(OFF)</sub>	_	10.1	_	ns	$R_G = 6\Omega$ , $I_D = 1A$	
Turn-Off Fall Time	t <sub>F</sub>	-	4.5		ns		
Body Diode Reverse Recovery Time	t <sub>RR</sub>	_	12.9	_	ns	$I_F = 2.6A$ , $di/dt = 100A/\mu s$	
Body Diode Reverse Recovery Charge		_	5.4	_	nC	$I_F = 2.6A$ , $di/dt = 100A/\mu s$	

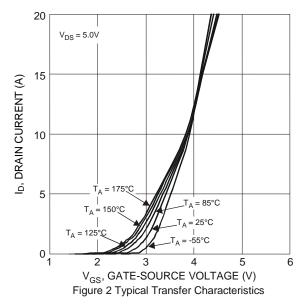
Short duration pulse test used to minimize self-heating effect.
 Guaranteed by design. Not subject to product testing.

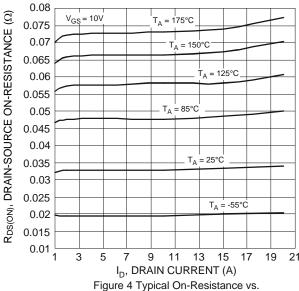












0.1  $R_{DS(ON)}$ , DRAIN-SOURCE ON-RESISTANCE  $(\Omega)$ 0.09 0.08  $V_{GS} = 4.5V$  $I_D = 4.4A$ 0.07 0.06 0.05 V<sub>GS</sub> = 10V 0.04 I<sub>D</sub> = 5.1A 0.03 0.02 0.01 0 -50 -25 0 25 50 75 100 125 150 175 T<sub>J</sub>, JUNCTION TEMPERATURE (°C)

Drain Current and Temperature



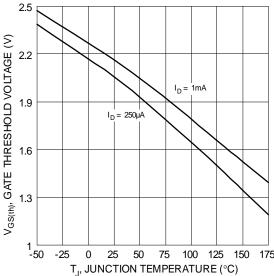


Figure 7 Gate Threshold Variation vs. Junction Temperature

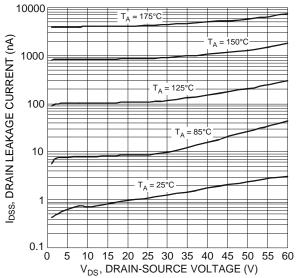


Figure 9 Typical Drain-Source Leakage Current vs. Voltage

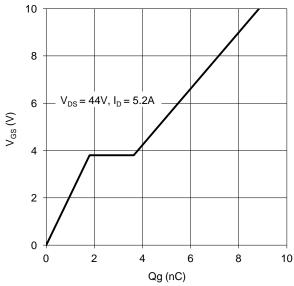
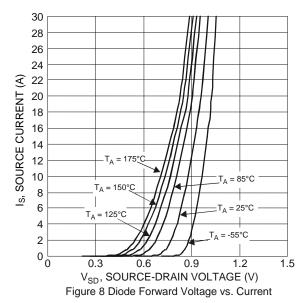
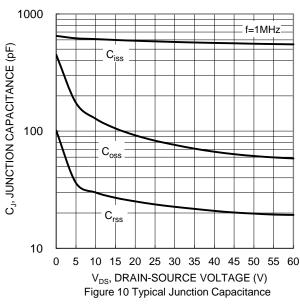
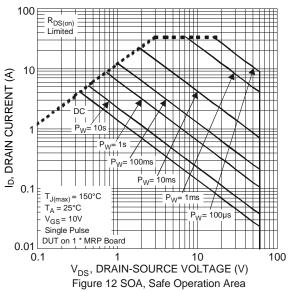


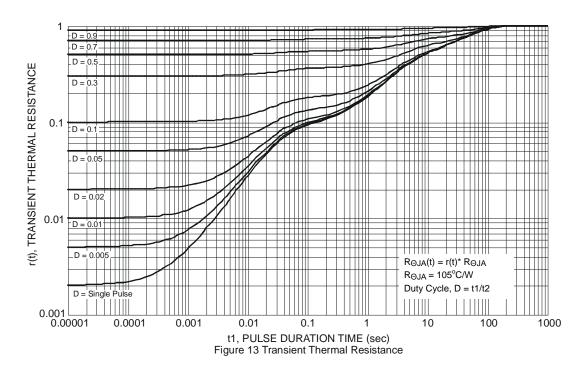
Figure 11 Gate Charge









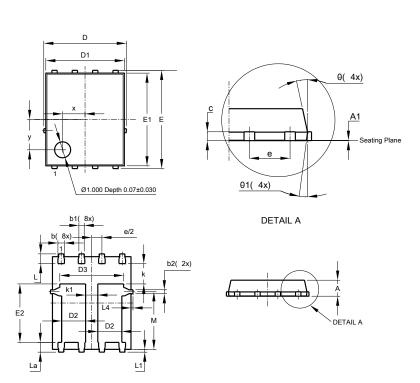




## **Package Outline Dimensions**

Please see http://www.diodes.com/package-outlines.html for the latest version.

## PowerDI5060-8 (Type C)

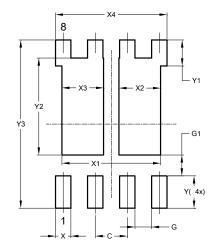


PowerDI5060-8 (Type C)					
Dim	Min	Max	Тур		
Α	0.90	1.10	1.00		
A1	0	0.05	0.02		
b	0.33	0.51	0.41		
b1	0.300	0.366	0.333		
b2	0.20	0.35	0.25		
С	0.23	0.33	0.277		
D	5	.15 BS0	2		
D1	4.85	4.95	4.90		
D2	1.40	1.60	1.50		
D3	_	_	3.98		
Е	6.15 BSC				
E1	5.75	5.85	5.80		
E2	3.56	3.76	3.66		
е	1	1.27BSC			
k	_	_	1.27		
k1	0.56	_	_		
L	0.51	0.71	0.61		
La	0.51	0.71	0.61		
L1	0.05	0.20	0.175		
L4	_	_	0.125		
M	3.50	3.71	3.605		
х	1	_	1.400		
у	_	_	1.900		
θ	10°	12°	11°		
θ1	6°	8°	7°		
All Dimensions in mm					

## **Suggested Pad Layout**

Please see http://www.diodes.com/package-outlines.html for the latest version.

#### PowerDI5060-8 (Type C)



Dimensions	Value		
Dilliensions	(in mm)		
С	1.270		
G	0.660		
G1	0.820		
Χ	0.610		
X1	3.910		
X2	1.650		
Х3	1.650		
X4	4.420		
Υ	1.270		
Y1	1.020		
Y2	3.810		
Y3	6.610		



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